

74HC10PW-TP

Triple 3-input Nand Gate

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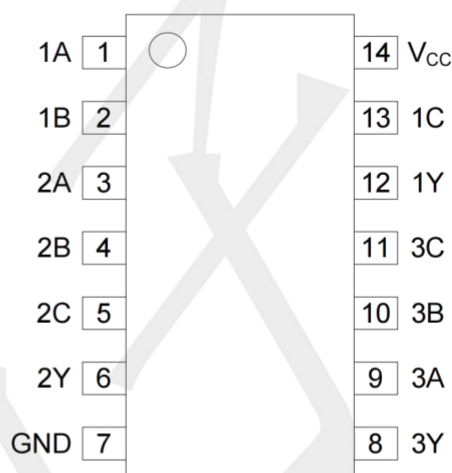
Features

- Wide supply voltage range from 2.0 V to 6.0 V
- CMOS low power dissipation
- Buffer input
- Support fan out for up to 10 LSTTL loads
- Compared with LSTTL logic IC, it can significantly reduce power consumption
- Packaging: TSSOP-14

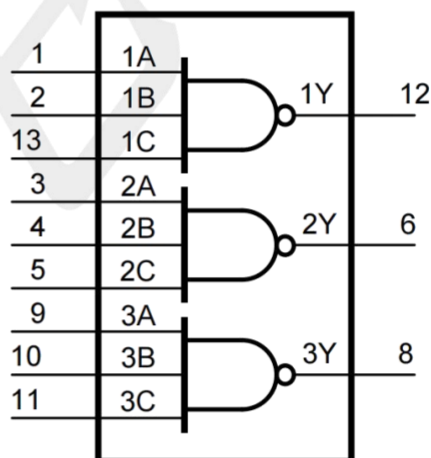
Applications

- S-R latch
- Alarm detection circuit
- Tampering detection circuit

PIN CONFIGURATIONS (Top view)



LOGIC SYMBOL



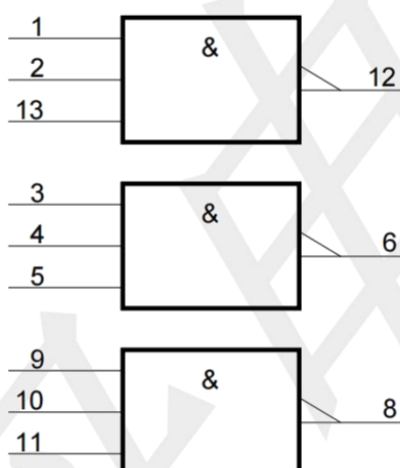
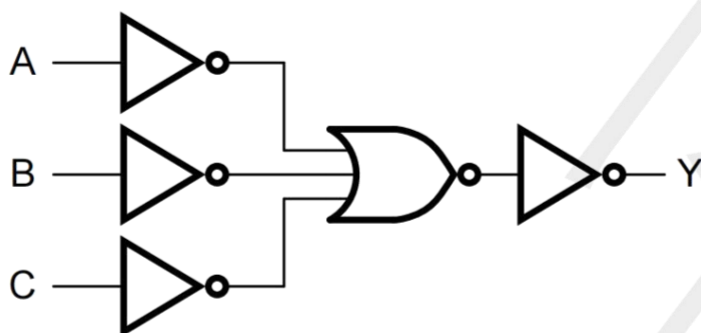
General Description

The 74HC10PW-TP is a triple 3-input NAND gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of VCC.

PIN DESCRIPTION

PIN NO.	PIN NAME	DESCRIPTION	PIN NO.	PIN NAME	DESCRIPTION
1	1A	Data input	8	3Y	Data output
2	1B	Data input	9	3A	Data input
3	2A	Data input	10	3B	Data input
4	2B	Data input	11	3C	Data input
5	2C	Data input	12	1Y	Data output
6	2Y	Data output	13	1C	Data input
7	GND	ground (0 V)	14	VCC	supply voltage

Functional diagram



Function table

Input			Output
nA	nB	nC	nY
L	X	X	H
X	L	X	H
X	X	L	H
H	H	H	L

Note: H=HIGH voltage level; L=LOW voltage level; X=don't care.

ABSOLUTE MAXIMUM RATINGS

(Voltages are referenced to GND(ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Max	Unit
Supply voltage	V _{CC}		-0.5	+7	V
Input clamping current	I _{IK}	V _I <-0.5V or V _I >V _{CC} +0.5V	--	±20	mA
Output clamping current	I _{OK}	V _O <-0.5V or V _O >V _{CC} +0.5V	--	±20	mA
Output current	I _O	-0.5V<V _O <V _{CC} +0.5V	--	±25	mA
Supply current	I _{CC}		--	50	mA
Ground current	I _{GND}		-50	--	mA
Total power dissipation	P _{tot}		--	500	mW
Storage temperature	T _{stg}		-65	+150	°C
Soldering temperature	T _L		260		°C

Recommended operating conditions

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Supply voltage	V_{CC}		2.0	5.0	6.0	V
Input voltage	V_I		0	--	V_{CC}	V
Output voltage	V_O		0	--	V_{CC}	V
Input transition rise and fall rate	$\Delta t / \Delta V$	$V_{CC} = 2.0V$	--	--	625	ns/V
		$V_{CC} = 4.5V$	--	1.67	139	ns/V
		$V_{CC} = 6.0V$	--	--	83	ns/V
Ambient temperature	T_{amb}		-40	--	+125	°C

Electrical Characteristics (DC)

($T_{amb}=25^{\circ}\text{C}$, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
HIGH-level input voltage	V_{IH}	$V_{CC}=2.0\text{V}$	1.5	1.2	--	V
		$V_{CC}=4.5\text{V}$	3.15	2.4	--	V
		$V_{CC}=6.0\text{V}$	4.2	3.2	--	V
LOW-level input voltage	V_{IL}	$V_{CC}=2.0\text{V}$	--	0.8	0.5	V
		$V_{CC}=4.5\text{V}$	--	2.1	1.35	V
		$V_{CC}=6.0\text{V}$	--	2.8	1.8	V
HIGH-level output voltage	V_{OH}	$V_I=V_{IH}$ or V_{IL} $I_O=-20\mu\text{A}; V_{CC}=2.0\text{V}$	1.9	2.0	--	V
		$I_O=-20\mu\text{A}; V_{CC}=4.5\text{V}$	4.4	4.5	--	V
		$I_O=-20\mu\text{A}; V_{CC}=6.0\text{V}$	5.9	6.0	--	V
		$I_O=-4.0\text{mA}; V_{CC}=4.5\text{V}$	3.98	4.32	--	V
		$I_O=-5.2\text{mA}; V_{CC}=6.0\text{V}$	5.48	5.81	--	V
LOW-level output voltage	V_{OL}	$V_I=V_{IH}$ or V_{IL} $I_O=20\mu\text{A}; V_{CC}=2.0\text{V}$	--	0	0.1	V
		$I_O=20\mu\text{A}; V_{CC}=4.5\text{V}$	--	0	0.1	V
		$I_O=20\mu\text{A}; V_{CC}=6.0\text{V}$	--	0	0.1	V
		$I_O=4.0\text{mA}; V_{CC}=4.5\text{V}$	--	0.15	0.26	V
		$I_O=5.2\text{mA}; V_{CC}=6.0\text{V}$	--	0.16	0.26	V
Input leakage current	I_I	$V_I=V_{CC}$ or GND; $V_{CC}=6.0\text{V}$	--	--	± 1	μA
Supply current	I_{CC}	$V_I=V_{CC}$ or GND; $I_O=0\text{A}; V_{CC}=6.0\text{V}$	--	--	2.0	μA
Input capacitance	C_I		--	3.5	--	pF

Electrical Characteristics (AC)

($T_{amb}=25^{\circ}\text{C}$, voltages are referenced to GND (ground=0V), unless otherwise specified.)

Parameter	Symbol	Conditions		Min	Typ	Max	Unit
nA, nB, nC to nY propagation delay	t_{pd}	see Figure 5 ^[1]	$V_{CC}=2.0\text{V}$	--	30	95	ns
			$V_{CC}=4.5\text{V}$	--	11	19	ns
			$V_{CC}=5.0\text{V}; C_L=15\text{pF}$	--	9	--	ns
			$V_{CC}=6.0\text{V}$	--	9	16	ns
Transition time	t_t	see Figure 5 ^[2]	$V_{CC}=2.0\text{V}$	--	19	75	ns
			$V_{CC}=4.5\text{V}$	--	7	15	ns
			$V_{CC}=6.0\text{V}$	--	6	13	ns
Power dissipation capacitance	C_{PD}	per package; $V_i = \text{GND to } V_{CC}$ ^[3]		--	12	--	pF

Note:

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_t is the same as t_{THL} and t_{TLH} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in

μW). $P_D = (C_{PD} \times V_{CC}^2 \times f_i \times N) + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i =input frequency in MHz; f_o =output

frequency in MHz; C_L =output load

capacitance in pF; V_{CC} =supply

voltage in V; N =number of inputs

switching;

$\sum (C_L \times V_{CC}^2 \times f_o)$ =sum of outputs.

Testing Circuit

AC Testing Circuit

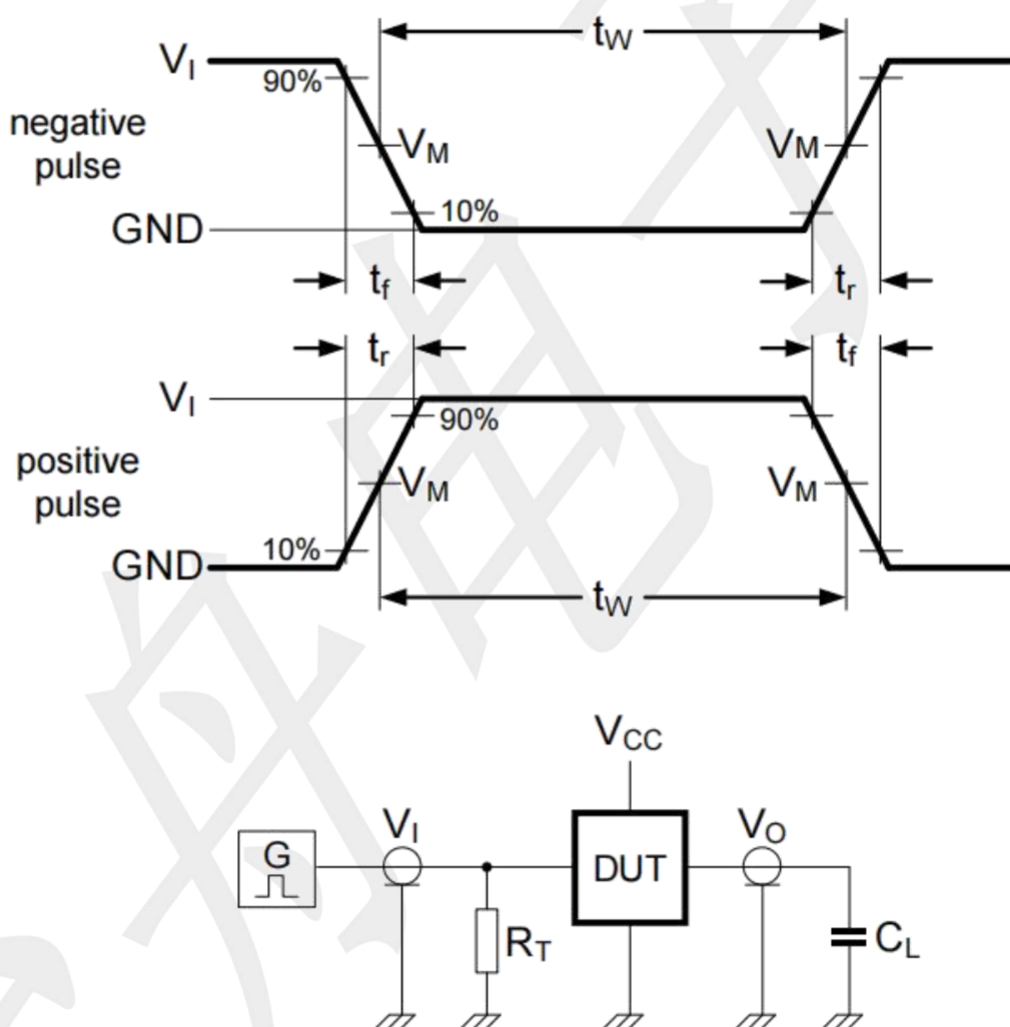


Figure 4. Test circuit for measuring switching times

Definitions for test circuit:

C_L =load capacitance including jig and probe capacitance.

R_T =termination resistance should be equal to the output impedance Z_o of the pulse generator.

Testing Circuit

AC Testing Waveforms

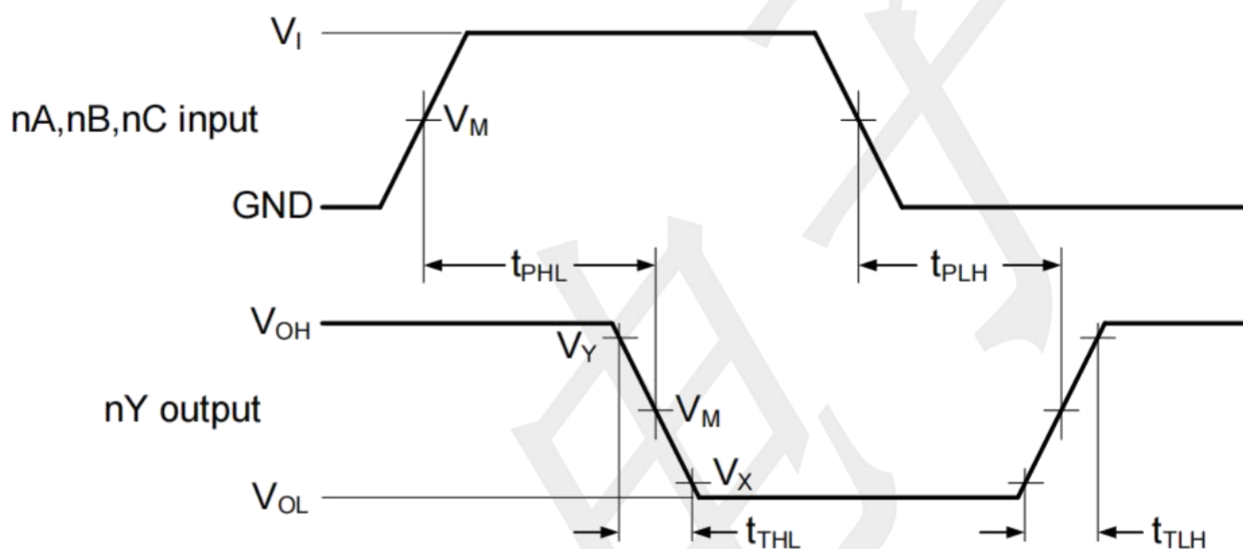


Figure 5. Input to output propagation delays

Measurement Points

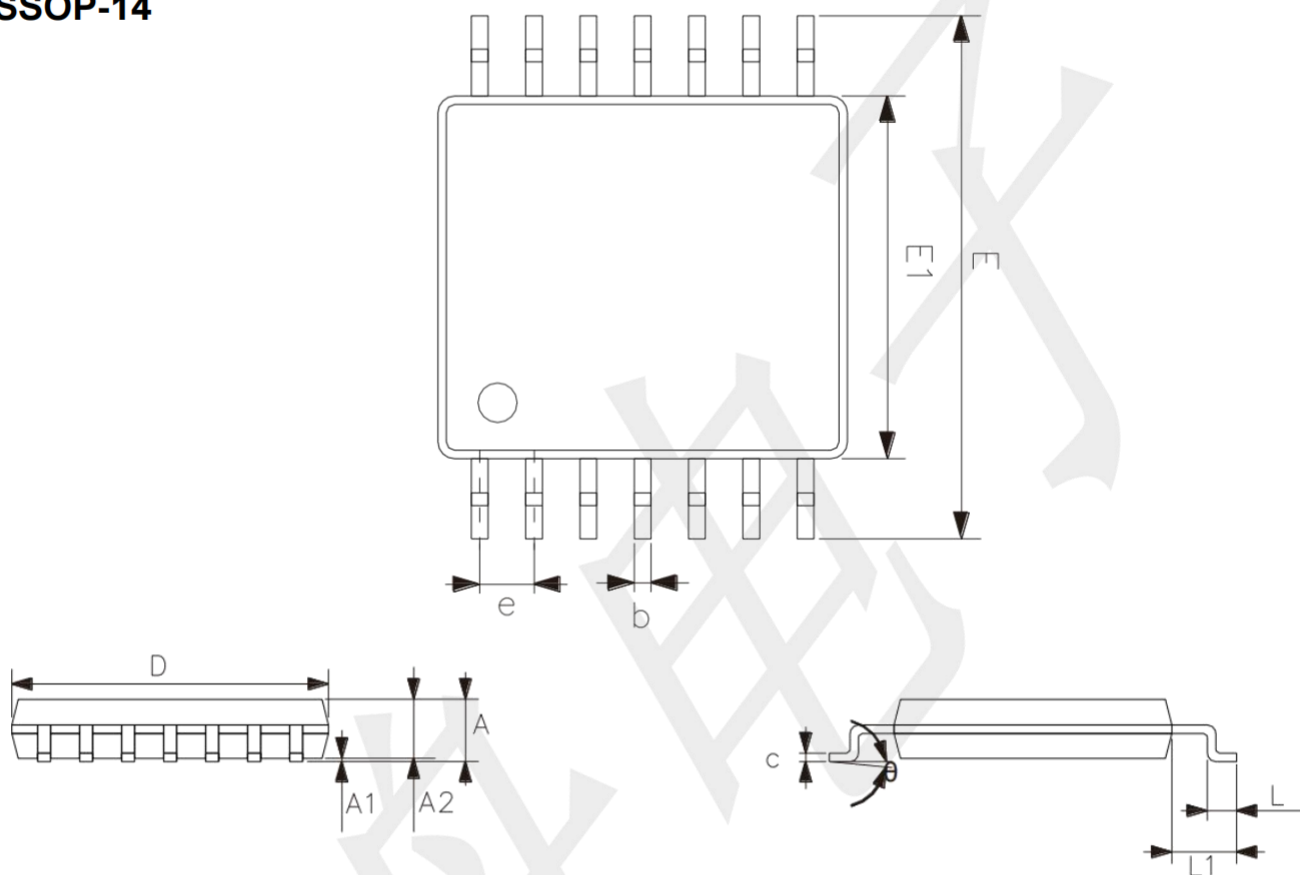
Type	Input	Output		
	V_M	V_M	V_X	V_Y
	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$

Test Data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
	V_{CC}	6.0ns	15pF, 50pF	t_{PLH}, t_{PHL}

Package information

TSSOP-14



Symbol	Dimensions (mm)	
	Min.	Max.
A	-	1.20
A1	0.05	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E1	4.30	4.50
E	6.20	6.60
e	0.65	
L	0.45	0.75
L1	1.00	
θ	0°	8°